

The documentation and process conversion measures necessary to comply with this revision shall be completed by 17 March 2016.

INCH-POUND

MIL-PRF-19500/603K  
 17 December 2015  
 SUPERSEDING  
 MIL-PRF-19500/603J  
 6 May 2013

PERFORMANCE SPECIFICATION SHEET

\* TRANSISTOR, FIELD EFFECT RADIATION HARDENED  
 (TOTAL DOSE ONLY), N-CHANNEL, SILICON, (THROUGH-HOLE AND SURFACE MOUNT PACKAGES)  
 TYPES 2N7268, 2N7269, 2N7270, 2N7394,  
 JANTXVR, F, G, H; JANSR, F, G, AND H

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

\* 1.1 Scope. This specification covers the performance requirements for an N-channel, enhancement-mode, MOSFET, radiation hardened (total dose only), power. Two levels of product assurance (JANTXV and JANS) are provided for each device type, with avalanche energy maximum rating ( $E_{AS}$ ) and maximum avalanche current ( $I_{AS}$ ). Provisions for radiation hardness assurance (RHA) to four radiation levels ("R", "F", "G", and "H") are provided for JANTXV and JANS product assurance levels. See 6.7 for JANHC and JANKC die versions.

\* 1.2 Package outlines. The device package outlines are as follows: TO-254AA in accordance with [figure 1](#) and TO-276AB in accordance with [figure 2](#) for all encapsulated device types. See 6.7 for unencapsulated devices.

1.3 Maximum ratings. Unless otherwise specified,  $T_C = +25^\circ\text{C}$ .

| Type            | $P_T$<br>(1) | $P_T$<br>$T_A = +25^\circ\text{C}$ | $R_{\theta JA}$                      | $R_{\theta JC}$<br>(2)               | $V_{DS}$    | $V_{DG}$    | $V_{GS}$    | $I_{D1}$<br>(3) (4) | $I_{D2}$ (3) (4)<br>$T_C = +100^\circ\text{C}$ | $I_S$       |
|-----------------|--------------|------------------------------------|--------------------------------------|--------------------------------------|-------------|-------------|-------------|---------------------|--|-------------|
|                 | <u>W</u>     | <u>W</u>                           | <u><math>^\circ\text{C/W}</math></u> | <u><math>^\circ\text{C/W}</math></u> | <u>V dc</u> | <u>V dc</u> | <u>V dc</u> | <u>A dc</u>         | <u>A dc</u>                                    | <u>A dc</u> |
| 2N7394, 2N7394U | 150          | 4                                  | 35                                   | 0.83                                 | 60          | 60          | $\pm 20$    | 35.0                | 30.0   | 35.0        |
| 2N7268, 2N7268U | 150          | 4                                  | 35                                   | 0.83                                 | 100         | 100         | $\pm 20$    | 34.0                | 21.0   | 34.0        |
| 2N7269, 2N7269U | 150          | 4                                  | 35                                   | 0.83                                 | 200         | 200         | $\pm 20$    | 26.0                | 16.0   | 26.0        |
| 2N7270, 2N7270U | 150          | 4                                  | 35                                   | 0.83                                 | 500         | 500         | $\pm 20$    | 11.0                | 7.0  | 11.0        |

| Type            | $I_{DM}$     | $T_J$ and $T_{STG}$                | $V_{ISO}$<br>70,000 ft altitude |
|-----------------|--------------|------------------------------------|---------------------------------|
|                 | <u>A(pk)</u> | <u><math>^\circ\text{C}</math></u> | <u>V dc</u>                     |
| 2N7394, 2N7394U | 140          | -55 to +150                        | N/A                             |
| 2N7268, 2N7268U | 136          |                                    | N/A                             |
| 2N7269, 2N7269U | 104          |                                    | N/A                             |
| 2N7270, 2N7270U | 44           |                                    | 500                             |

See notes next page.

\* Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to [Semiconductor@dla.mil](mailto:Semiconductor@dla.mil). Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.



1.3 Maximum ratings. Unless otherwise specified, T<sub>C</sub> = +25°C - Continued.

- (1) Derate linearly 1.2 W/°C for T<sub>C</sub> > +25°C.
- (2) See [figure 3](#) for thermal impedance curves.
- (3) The following formula derives the maximum theoretical I<sub>D</sub> limit. I<sub>D</sub> is limited by package design:

$$I_D = \sqrt{\frac{T_{JM} - T_C}{(R_{\theta JC}) \times (R_{DS(on)} \text{ at } T_{JM})}}$$

- (4) See [figure 4](#) for maximum drain current graphs.

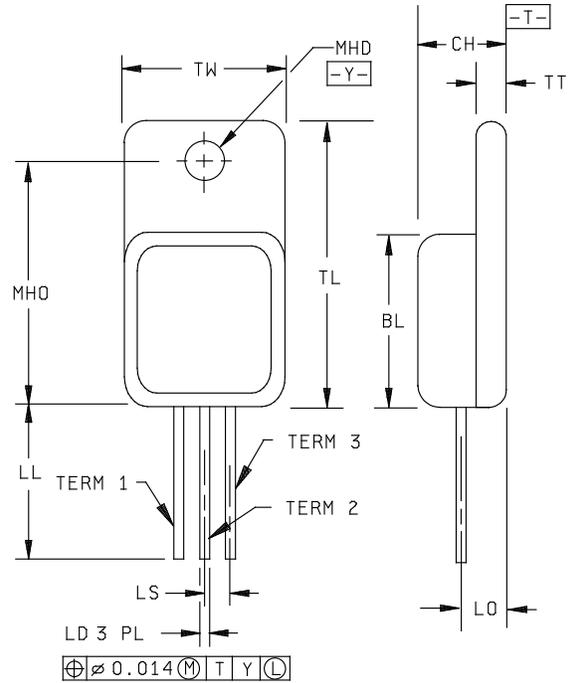
1.4 Primary electrical characteristics at T<sub>C</sub> = +25°C.

| Type            | Min<br>V <sub>(BR)DSS</sub><br>V <sub>GS</sub> = 0<br>I <sub>D</sub> = 1.0<br>mA dc | V <sub>GS</sub> (TH) <sub>1</sub><br>V <sub>DS</sub> ≥ V <sub>GS</sub><br>I <sub>D</sub> = 1.0<br>mA dc |             | Max I <sub>DSS1</sub><br>V <sub>GS</sub> = 0<br>V <sub>DS</sub> = 80<br>percent of rated<br>V <sub>DS</sub> | Max r <sub>DS(ON)</sub> (1)<br>V <sub>GS</sub> = 12 V dc |   | EAS<br>at I <sub>D1</sub> | I <sub>AS</sub> |
|-----------------|---|---|-------------|---|--|---|---------------------------|-----------------|
|                 |   |   |             |   | T <sub>J</sub> = +25°C<br>at I <sub>D2</sub>             | T <sub>J</sub> = +150°C<br>at I <sub>D2</sub> |                           |                 |
|                 |   | Min   | Max         |   | ohm  | ohm   |                           |                 |
|                 | <u>V dc</u>   | <u>V dc</u>   | <u>V dc</u> | <u>μA dc</u>  | <u>ohm</u>   | <u>ohm</u>                                    | <u>mJ</u>                 | <u>A</u>        |
| 2N7394, 2N7394U | 60  | 2.0   | 4.0         | 25  | 0.027  | 0.030   | 500                       | 35.0            |
| 2N7268, 2N7268U | 100   | 2.0   | 4.0         | 25  | 0.065  | 0.132   | 500                       | 34.0            |
| 2N7269, 2N7269U | 200   | 2.0   | 4.0         | 25  | 0.100  | 0.230   | 500                       | 26.0            |
| 2N7270, 2N7270U | 500   | 2.0   | 4.0         | 50  | 0.450  | 1.260   | 500                       | 11.0            |

(1) Pulsed (see [4.5.1](#)).

- \* 1.5 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-19500, and as specified herein. See [6.5](#) for PIN construction example and [6.6](#) for a list of available PINs.
- \* 1.5.1 JAN certification mark and quality level for encapsulated devices. The quality level designators for encapsulated devices that are applicable for this specification sheet from the lowest to the highest level are as follows: "JANTXV" and "JANS".
- \* 1.5.2 Radiation hardness assurance (RHA) designator. The RHA levels that are applicable for this specification sheet from lowest to highest are as follows: "R", "F", "G", and "H".
- \* 1.5.3 Device type. The designation system for the device types of transistors covered by this specification sheet are as follows.
  - \* 1.5.3.1 First number and first letter symbols. The transistors of this specification sheet use the first number and letter symbols "2N".
  - \* 1.5.3.2 Second number symbols. The second number symbols for the transistors covered by this specification sheet are as follows: "7268", "7269", "7270" and "7394".
  - \* 1.5.3.3 Suffix letters. No suffix letters are used on devices that are packaged in the TO-254AA package of [figure 1](#). The suffix letter "U" is used on devices that are packaged in the TO-276AB package of [figure 2](#).
- \* 1.5.4 Lead finish. The lead finishes applicable to this specification sheet are listed on [QPDSIS-19500](#).

| Symbol | Dimensions |      |             |       |
|--------|------------|------|-------------|-------|
|        | Inches     |      | Millimeters |       |
|        | Min        | Max  | Min         | Max   |
| BL     | .535       | .545 | 13.59       | 13.84 |
| CH     | .249       | .260 | 6.32        | 6.60  |
| LD     | .035       | .045 | 0.89        | 1.14  |
| LL     | .510       | .570 | 12.95       | 14.48 |
| LO     | .150 BSC   |      | 3.81 BSC    |       |
| LS     | .150 BSC   |      | 3.81 BSC    |       |
| MHD    | .139       | .149 | 3.53        | 3.78  |
| MHO    | .665       | .685 | 16.89       | 17.40 |
| TL     | .790       | .800 | 20.07       | 20.32 |
| TT     | .040       | .050 | 1.02        | 1.27  |
| TW     | .535       | .545 | 13.59       | 13.84 |
| Term 1 | Drain      |      |             |       |
| Term 2 | Source     |      |             |       |
| Term 3 | Gate       |      |             |       |



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Refer to applicable symbol list.
4. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi x$  symbology.
5. All terminals are isolated from case.

FIGURE 1. Physical dimensions for TO-254AA (2N7268, 2N7269, 2N7270, and 2N7394).

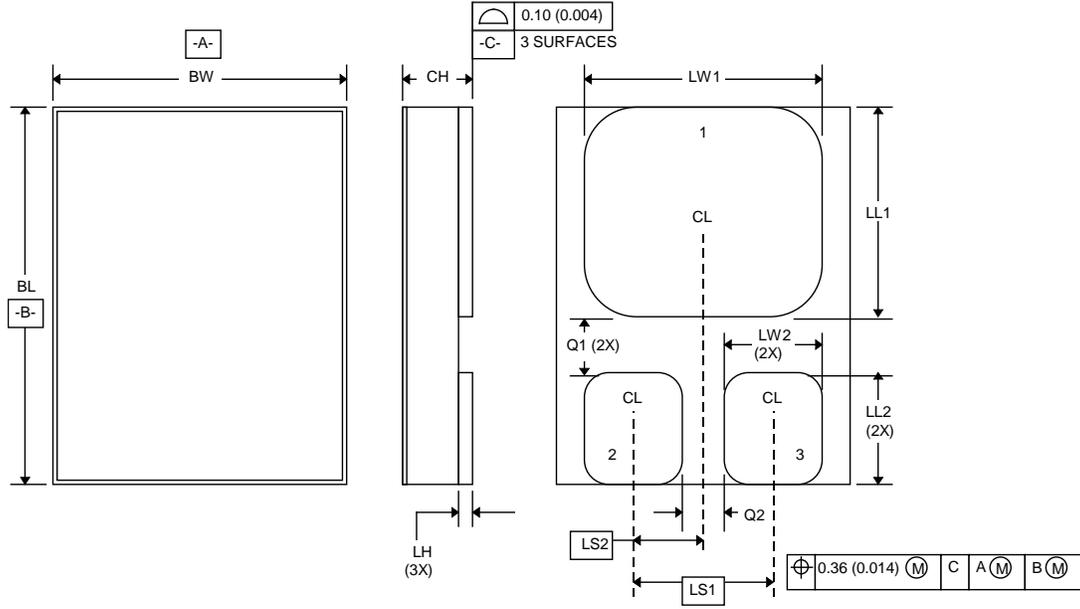


FIGURE 2. Dimensions and configuration of surface mount package outline, TO-276AB (2N7268U, 2N7269U, 2N7270U, AND 2N7394U).

MIL-PRF-19500/603K

| Dimensions      |          |      |             |       |
|-----------------|----------|------|-------------|-------|
| Symbol          | SMD-1    |      |             |       |
|                 | Inches   |      | Millimeters |       |
|                 | Min      | Max  | Min         | Max   |
| BL              | .620     | .630 | 15.75       | 16.00 |
| BW              | .445     | .455 | 11.30       | 11.56 |
| CH              |          | .142 |             | 3.60  |
| LH              | .010     | .020 | 0.26        | 0.50  |
| LL <sub>1</sub> | .410     | .420 | 10.41       | 10.67 |
| LL <sub>2</sub> | .152     | .162 | 3.86        | 4.11  |
| LS <sub>1</sub> | .210 BSC |      | 5.33 BSC    |       |
| LS <sub>2</sub> | .105 BSC |      | 2.67 BSC    |       |
| LW <sub>1</sub> | .370     | .380 | 9.40        | 9.65  |
| LW <sub>2</sub> | .135     | .145 | 3.43        | 3.68  |
| Q <sub>1</sub>  | .030     |      | 0.76        |       |
| Q <sub>2</sub>  | .035     |      | 0.89        |       |
| Term 1          | Drain    |      |             |       |
| Term 2          | Gate     |      |             |       |
| Term 3          | Source   |      |             |       |

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. The lid shall be electrically isolated from the drain, gate and source.
4. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi$ x symbology.

FIGURE 2. Dimensions and configuration of surface mount package outline, TO-276AB (2N7268U, 2N7269U, 2N7270U, AND 2N7394U) - Continued.

## 2. APPLICABLE DOCUMENTS

- \* 2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3 and 4 of this specification, whether or not they are listed.

### 2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

#### DEPARTMENT OF DEFENSE SPECIFICATIONS

[MIL-PRF-19500](#) - Semiconductor Devices, General Specification for.

#### DEPARTMENT OF DEFENSE STANDARDS

[MIL-STD-750](#) - Test Methods for Semiconductor Devices.

- \* (Copies of these documents are available online at <http://quicksearch.dla.mil/>).

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

## 3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in [MIL-PRF-19500](#) and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in [MIL-PRF-19500](#) and as follows.

$I_{AS}$  ..... Rated avalanche current, nonrepetitive  
nC ..... nano Coulomb.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in [MIL-PRF-19500](#) and on [figure 1](#) and [2](#) herein. Methods used for electrical isolation of the terminal feedthroughs shall employ materials that contain a minimum of 90 percent  $AL_2O_3$  (ceramic). Examples of such construction techniques are metallized ceramic eyelets or ceramic walled packages.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with [MIL-PRF-19500](#), [MIL-STD-750](#), and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.4.2 Internal construction. Multiple chip construction is not permitted.

3.5 Marking. Marking shall be in accordance with [MIL-PRF-19500](#).

3.6 Electrostatic discharge protection. The devices covered by this specification require electrostatic discharge protection.

3.6.1 Handling. MOS devices must be handled with certain precautions to avoid damage due to the accumulation of static charge. However, the following handling practices are recommended (see 3.6).

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools, and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber, or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source,  $R \leq 100 \text{ k}\Omega$ , whenever bias voltage is to be applied drain to source.

3.7 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and [table I](#) herein.

3.8 Electrical test requirements. The electrical test requirements shall be as specified in [table I](#).

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

#### 4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see [4.3](#)).
- c. Conformance inspection (see [4.4](#) and [tables I and II](#)).

4.2 Qualification inspection. Qualification inspection shall be in accordance with [MIL-PRF-19500](#).

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of [table III](#) tests, the tests specified in [table III](#) herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.3 Screening (JANTXV and JANS levels only). Screening shall be in accordance with appendix E, table E-IV of MIL-PRF-19500 and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

| Screen (see table IV of MIL-PRF-19500)<br>(1) (2) | Measurement  |   |
|---|--|---|
|   | JANS level   | JANTXV levels   |
| (3)   | Gate stress test (see 4.3.1).  | Gate stress test (see 4.3.1).   |
| (3)   | Single pulse avalanche energy test, method 3470 of MIL-STD-750 (see 4.3.2).  | Single pulse avalanche energy test, method 3470 of MIL-STD-750 (see 4.3.2).   |
| (3) 3c  | Method 3161 of MIL-STD-750 (see 4.3.3).  | Method 3161 of MIL-STD-750 (see 4.3.3).   |
| 9   | Subgroup 2 of table I herein. $I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ .   | Subgroup 2 of table I herein.   |
| 10  | Method 1042 of MIL-STD-750, test condition B   | Method 1042 of MIL-STD-750, test condition B  |
| 11  | $I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ , $r_{DS(on)1}$ , $V_{GS(TH)1}$<br>Subgroup 2 of table I herein<br>$\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta I_{DSS1} = \pm 10$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater.   | $I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ , $r_{DS(on)1}$ , $V_{GS(TH)1}$<br>Subgroup 2 of table I herein.   |
| 12  | Method 1042 of MIL-STD-750, test condition A.  | Method 1042 of MIL-STD-750, test condition A.   |
| 13  | Subgroups 2 and 3 of table I herein<br>$\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta I_{DSS1} = \pm 10$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta r_{DS(on)1} = \pm 20$ percent of initial value<br>$\Delta V_{GS(th)1} = \pm 20$ percent of initial value. | Subgroup 2 of table I herein<br>$\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta I_{DSS1} = \pm 10$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater.<br>$\Delta r_{DS(on)1} = \pm 20$ percent of initial value<br>$\Delta V_{GS(th)1} = \pm 20$ percent of initial value. |
| 17  | Method 1081 of MIL-STD-750 (see 4.3.4),<br>Endpoints: Subgroup 2 of table I herein. (Not applicable for TO-276AB surface mount devices).   | Method 1081 of MIL-STD-750 (see 4.3.4),<br>Endpoints: Subgroup 2 of table I herein. (Not applicable for TO-276AB surface mount devices).  |

(1) At the end of the test program,  $I_{GSSF1}$ ,  $I_{GSSR1}$ , and  $I_{DSS1}$  are measured.

\* (2) An out-of-family program to characterize  $I_{GSSF1}$ ,  $I_{GSSR1}$ ,  $I_{DSS1}$ ,  $V_{GS(th)1}$ , and  $r_{DS(ON)1}$  shall be invoked.

(3) Shall be performed anytime after temperature cycling, screen 3a; JANTXV level does not need to be repeated in screening requirements.

4.3.1 Gate stress test. Apply  $V_{GS} = 30$  V minimum for  $t = 250$   $\mu$ s minimum.

4.3.2 Single pulse avalanche energy  $E_{AS}$ .

- a. Peak current ( $I_{AS}$ ) .....  $I_{AS(max)}$ .
- b. Peak gate voltage ( $V_{GS}$ ) ..... 12 V.
- c. Gate to source resistor ( $R_{GS}$ ) .....  $25\Omega \leq R_{GS} \leq 200\Omega$ .
- d. Initial case temperature ( $T_C$ ) .....  $+25^\circ\text{C}$ ,  $+10^\circ\text{C}$ ,  $-5^\circ\text{C}$ .
- e. Inductance (L) .....  $L = (2 * E_{AS} / (I_{D1})^2) * ((V_{BR} - V_{DD}) / V_{BR})$  mH minimum.
- f. Number of pulses to be applied ..... 1 pulse minimum.
- g. Supply voltage ( $V_{DD}$ ) ..... 25 V for 2N7268, 2N7394, and 2N7268U; 50 V for 2N7269, 2N7269U, and 2N7270.

4.3.3 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3161 of [MIL-STD-750](#) using the guidelines in that method for determining  $I_M$ ,  $I_H$ ,  $t_H$ ,  $t_{SW}$ , (and  $V_H$  where appropriate). Measurement delay time ( $t_{MD}$ ) = 70  $\mu$ s max. See [table III](#), group E, subgroup 4 herein.

4.3.4 Dielectric withstanding voltage.

- a. Magnitude of test voltage ..... 900 V dc.
- b. Duration of application of test voltage ..... 15 seconds (min).
- c. Points of application of test voltage ..... All leads to case (bunch connection).
- d. Method of connection ..... Mechanical.
- e. Kilovolt-ampere rating of high voltage source ..... 1,200V /1.0 mA (min).
- f. Maximum leakage current ..... 1.0 mA.
- g. Voltage ramp up time ..... 500V /second.

4.4 Conformance inspection. Conformance inspection shall be in accordance with [MIL-PRF-19500](#), and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with appendix E, table V of [MIL-PRF-19500](#) and [table I](#) herein. End-point electrical measurements shall be in accordance with [table I](#), subgroup 2 herein.

\* 4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in [table VIA](#) (JANS) and [table VIB](#) (JANTXV) of [MIL-PRF-19500](#), and herein.

\* 4.4.2.1 Quality level JANS, table E-VIA of MIL-PRF-19500.

| <u>Subgroup</u> | <u>Method</u> | <u>Condition</u>  |
|-----------------|---------------|---|
| B3              | 1051          | Test condition G, 100 cycles.   |
| B3              | 2075          | See 3.4.2.  |
| B3              | 2077          | SEM qualification may be performed anytime prior to lot formation.  |
| B4              | 1042          | The heating cycle shall be 30 seconds minimum.  |
| B5              | 1042          | Accelerated steady-state gate bias, condition B, $V_{GS} = \text{rated}$ , $T_A = +175^\circ\text{C}$ , $t = 24$ hours minimum; or, $T_A = +150^\circ\text{C}$ , $t = 48$ hours minimum.      |
| B5              | 1042          | Accelerated steady-state reverse bias, condition A, $V_{DS} = \text{rated}$ , $T_A = +175^\circ\text{C}$ , $t = 120$ hours minimum; or, $T_A = +150^\circ\text{C}$ , $t = 240$ hours minimum. |
| B6              |               | Not applicable for surface mount packages.  |

\* 4.4.2.2 Quality level JANTXV, table E-VIB of MIL-PRF-19500.

| <u>Subgroup</u> | <u>Method</u> | <u>Condition</u>  |
|-----------------|---------------|---|
| B2              | 1051          | Test condition G, 25 cycles.  |
| B3              | 1042          | The heating cycle shall be 30 seconds minimum.  |
| B3              | 2037          | Test condition D. All internal bond wires for each device shall be pulled separately. |
| B4              | 2075          | See 3.4.2.  |
| B5              |               | Not applicable for surface mount packages.  |

\* 4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500 and as follows.

| <u>Subgroup</u> | <u>Method</u> | <u>Condition</u>   |
|-----------------|---------------|--|
| C2              | 2036          | Test condition A; weight = 10 pounds; $t = 15$ s (applicable to TO-254AA only).              |
| C5              | 3161          | $R_{\theta JC(\text{max})} = 0.83^\circ\text{C/W}$ . Not required when performed in Group B. |
| C6              | 1042          | The heating cycle shall be 30 seconds minimum.   |

4.4.4 Group D Inspection. Group D inspection shall be conducted in accordance with appendix E, table VIII of MIL-PRF-19500 and table II herein.

\* 4.4.5 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table IX of MIL-PRF-19500 and as specified in table III herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in MIL-STD-750.

TABLE I. Group A inspection.

| Inspection 1/                              | MIL-STD-750 |  | Symbol          | Limits |       | Unit          |
|--|-------------|--|-----------------|--------|-------|---------------|
|  | Method      | Conditions   |                 | Min    | Max   |               |
| <u>Subgroup 1</u>                          |             |  |                 |        |       |               |
| Visual and mechanical inspection           | 2071        |  |                 |        |       |               |
| <u>Subgroup 2</u>                          |             |  |                 |        |       |               |
| Thermal impedance 2/                       | 3161        | See 4.3.3.   | $Z_{\theta JC}$ |        |       | $^{\circ}C/W$ |
| Breakdown voltage, drain to source         | 3407        | $V_{GS} = 0$ ; $I_D = 1$ mA dc<br>bias condition C                         | $V_{(BR)DSS}$   |        |       |               |
| 2N7394, 2N7394U                            |             |  |                 | 60     |       | V dc          |
| 2N7268, 2N7268U                            |             |  |                 | 100    |       | V dc          |
| 2N7269, 2N7269U                            |             |  |                 | 200    |       | V dc          |
| 2N7270, 2N7270U                            |             |  |                 | 500    |       | V dc          |
| Gate to source voltage threshold           | 3403        | $V_{DS} \geq V_{GS}$<br>$I_D = 1$ mA dc                                    | $V_{GS(TH)1}$   | 2.0    | 4.0   | V dc          |
| Gate current                               | 3411        | $V_{GS} = +20$ V dc, bias condition C,<br>$V_{DS} = 0$                     | $I_{GSSF1}$     |        | + 100 | nA dc         |
| Gate current                               | 3411        | $V_{GS} = -20$ V dc, bias condition C,<br>$V_{DS} = 0$                     | $I_{GSSR1}$     |        | - 100 | nA dc         |
| Drain current                              | 3413        | $V_{GS} = 0$ , bias condition C<br>$V_{DS} = 80$ percent of rated $V_{DS}$ | $I_{DSS1}$      |        |       |               |
| 2N7394, 2N7394U                            |             |  |                 |        | 25    | $\mu A$ dc    |
| 2N7268, 2N7268U                            |             |  |                 |        | 25    | $\mu A$ dc    |
| 2N7269, 2N7269U                            |             |  |                 |        | 25    | $\mu A$ dc    |
| 2N7270, 2N7270U                            |             |  |                 |        | 50    | $\mu A$ dc    |
| Static drain to source on-state resistance | 3421        | $V_{GS} = 12$ V dc, condition A<br>pulsed (see 4.5.1), $I_D = I_{D2}$      | $r_{DS(on)1}$   |        |       |               |
| 2N7394, 2N7394U                            |             |  |                 |        | 0.027 | ohm           |
| 2N7268, 2N7268U                            |             |  |                 |        | 0.065 | ohm           |
| 2N7269, 2N7269U                            |             |  |                 |        | 0.100 | ohm           |
| 2N7270, 2N7270U                            |             |  |                 |        | 0.450 | ohm           |
| Static drain to source on-state resistance | 3421        | $V_{GS} = 12$ V dc, condition A<br>pulsed (see 4.5.1), $I_D = I_{D1}$      | $r_{DS(on)2}$   |        |       |               |
| 2N7394, 2N7394U                            |             |  |                 |        | 0.030 | ohm           |
| 2N7268, 2N7268U                            |             |  |                 |        | 0.070 | ohm           |
| 2N7269, 2N7269U                            |             |  |                 |        | 0.110 | ohm           |
| 2N7270, 2N7270U                            |             |  |                 |        | 0.500 | ohm           |
| * Forward voltage                          | 4011        | $I_D = I_{D1}$ , $V_{GS} = 0$ V dc, condition A                            | $V_{SD}$        |        |       |               |
| 2N7394, 2N7394U                            |             |  |                 |        | 1.4   | V             |
| 2N7268, 2N7268U                            |             |  |                 |        | 1.4   | V             |
| 2N7269, 2N7269U                            |             |  |                 |        | 1.4   | V             |
| 2N7270, 2N7270U                            |             |  |                 |        | 1.6   | V             |

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

| Inspection 1/  | MIL-STD-750 |  | Symbol        | Limits |           | Unit  |     |
|--|-------------|--|---------------|--------|-----------|-------|-----|
|  | Method      | Conditions   |               | Min    | Max       |       |     |
| <u>Subgroup 3</u>  |             |  |               |        |           |       |     |
| High temperature operation:  |             |  |               |        |           |       |     |
| Gate current   | 3411        | $T_C = T_J = +125^\circ\text{C}$<br>$V_{GS} = +20$ and $-20$ V dc<br>bias condition C, $V_{DS} = 0$                        | $I_{GSS2}$    |        | $\pm 200$ | nA dc |     |
| Drain current  | 3413        | $V_{GS} = 0$ ; bias condition C<br>$V_{DS} = 100$ percent of rated $V_{DS}$<br><br>$V_{DS} = 80$ percent of rated $V_{DS}$ | $I_{DSS2}$    |        | 1.0       | mA dc |     |
|  |             |  | $I_{DSS3}$    |        | 0.25      | mA dc |     |
| * Static drain to source on-state resistance<br><br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U | 3421        | $V_{GS} = 12$ V dc, condition A pulsed (see 4.5.1), $I_D = I_{D2}$   | $r_{DS(on)3}$ |        |           |       |     |
|  |             |  |               |        |           | 0.060 | ohm |
|  |             |  |               |        |           | 0.132 | ohm |
|  |             |  |               |        |           | 0.200 | ohm |
|  |             |  |               |        |           | 1.000 | ohm |
| Gate to source voltage (threshold)   | 3404        | $V_{DS} \geq V_{GS}$ , $I_D = 1$ mA dc   | $V_{GS(TH)2}$ | 1.0    |           | V dc  |     |
| Low temperature operation:   |             |  |               |        |           |       |     |
| Gate to source voltage (threshold)   | 3404        | $V_{DS} \geq V_{GS}$ , $I_D = 1$ mA dc   | $V_{GS(TH)3}$ |        | 5.0       | V dc  |     |
| <u>Subgroup 4</u>  |             |  |               |        |           |       |     |
| Forward transconductance<br><br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U                     | 3475        | $I_D = \text{rated } I_{D2}$ , $V_{DD} = 15$ V (see 4.5.1)   | gFS           |        |           |       |     |
|  |             |  |               |        | 12        | S     |     |
|  |             |  |               |        | 8         | S     |     |
|  |             |  |               |        | 8         | S     |     |
|  |             |  |               |        | 4         | S     |     |
| Switching time test  | 3472        | $I_D = I_{D1}$ , $V_{GS} = 12$ V dc<br>$R_G = 2.35\Omega$ , $V_{DD} = 50$ percent of rated $V_{DS}$                        |               |        |           |       |     |
| Turn-on delay time<br><br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U                           |             |  | $t_{d(on)}$   |        |           |       |     |
|  |             |  |               |        | 27        | ns    |     |
|  |             |  |               |        | 45        | ns    |     |
|  |             |  |               |        | 33        | ns    |     |
|  |             |  |               |        | 45        | ns    |     |

See footnotes at end of table.

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TABLE I. Group A inspection - Continued.

| Inspection 1/                           | MIL-STD-750 |   | Symbol       | Limits |     | Unit |
|---|-------------|---|--------------|--------|-----|------|
|   | Method      | Conditions  |              | Min    | Max |      |
| <u>Subgroup 4</u> - Continued           |             |   |              |        |     |      |
| Rise time                               |             |   | $t_r$        |        |     |      |
| 2N7394, 2N7394U                         |             |   |              |        | 100 | ns   |
| 2N7268, 2N7268U                         |             |   |              |        | 190 | ns   |
| 2N7269, 2N7269U                         |             |   |              |        | 140 | ns   |
| 2N7270, 2N7270U                         |             |   |              |        | 190 | ns   |
| Turn-off delay time                     |             |   | $t_{d(off)}$ |        |     |      |
| 2N7394, 2N7394U                         |             |   |              |        | 75  | ns   |
| 2N7268, 2N7268U                         |             |   |              |        | 170 | ns   |
| 2N7269, 2N7269U                         |             |   |              |        | 140 | ns   |
| 2N7270, 2N7270U                         |             |   |              |        | 190 | ns   |
| Fall time                               |             |   | $t_f$        |        |     |      |
| 2N7394, 2N7394U                         |             |   |              |        | 75  | ns   |
| 2N7268, 2N7268U                         |             |   |              |        | 130 | ns   |
| 2N7269, 2N7269U                         |             |   |              |        | 140 | ns   |
| 2N7270, 2N7270U                         |             |   |              |        | 130 | ns   |
| <u>Subgroup 5</u>                       |             |   |              |        |     |      |
| Safe operating area test (high voltage) | 3474        | See figures 5, 6, 7, and 8<br>$t_p = 10$ ms minimum<br>$V_{DS} = 80$ percent of maximum rated<br>$V_{DS}$ , ( $V_{DS} \leq 200$ ) |              |        |     |      |
| Electrical measurements                 |             | See table I, subgroup 2   |              |        |     |      |
| <u>Subgroup 6</u>                       |             |   |              |        |     |      |
| Not applicable                          |             |   |              |        |     |      |
| <u>Subgroup 7</u>                       |             |   |              |        |     |      |
| Gate charge                             | 3471        | Condition B   |              |        |     |      |
| On-state gate charge                    |             |   | $Q_{g(on)}$  |        |     |      |
| 2N7394, 2N7394U                         |             |   |              |        | 200 | nC   |
| 2N7268, 2N7268U                         |             |   |              |        | 160 | nC   |
| 2N7269, 2N7269U                         |             |   |              |        | 170 | nC   |
| 2N7270, 2N7270U                         |             |   |              |        | 150 | nC   |

See footnotes at end of table.

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TABLE I. Group A inspection - Continued.

| Inspection <u>1/</u>  | MIL-STD-750 |  | Symbol          | Limits |                            | Unit                 |
|---|-------------|--|-----------------|--------|----------------------------|----------------------|
|   | Method      | Conditions   |                 | Min    | Max                        |                      |
| <u>Subgroup 7</u> - Continued   |             |  |                 |        |                            |                      |
| Gate to source charge<br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U   |             |  | Q <sub>gs</sub> |        | 60<br>35<br>30<br>30       | nC<br>nC<br>nC<br>nC |
| Gate to drain charge<br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U    |             |  | Q <sub>gd</sub> |        | 75<br>65<br>60<br>75       | nC<br>nC<br>nC<br>nC |
| * Reverse recovery time<br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U | 3473        | Condition A, di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ 30 V,<br>I <sub>D</sub> = I <sub>D1</sub> | t <sub>rr</sub> |        | 280<br>570<br>820<br>1,100 | ns<br>ns<br>ns<br>ns |

1/ For sampling plan, see [MIL-PRF-19500](#).

2/ This test required for the following end-point measurements only:  
Group B, subgroups 2 and 3 (JANTXV).  
Group B, subgroups 3 and 4 (JANS).  
Group C, subgroup 2 and 6.  
Group E, subgroup 1.

TABLE II. Group D inspection.

| Inspection<br>1/ 2/   | MIL-STD-750 |  | Symbol             | Preirradiation limits |      |                           |      | Postirradiation limits |      |                           |      | Unit  |
|---|-------------|--|--------------------|-----------------------|------|---------------------------|------|------------------------|------|---------------------------|------|-------|
|   | Method      | Conditions   |                    | R                     |      | F, G, and H <sup>3/</sup> |      | R                      |      | F, G, and H <sup>3/</sup> |      |       |
|   |             |  |                    | Min                   | Max  | Min                       | Max  | Min                    | Max  | Min                       | Max  |       |
| <u>Subgroup 1</u>   |             |  |                    |                       |      |                           |      |                        |      |                           |      |       |
| Not applicable  |             |  |                    |                       |      |                           |      |                        |      |                           |      |       |
| <u>Subgroup 2</u>   |             | T <sub>C</sub> = +25°C   |                    |                       |      |                           |      |                        |      |                           |      |       |
| Steady-state total dose irradiation (V <sub>GS</sub> bias) 4/ | 1019        | V <sub>GS</sub> = 12 V<br>V <sub>DS</sub> = 0  |                    |                       |      |                           |      |                        |      |                           |      |       |
| Steady-state total dose irradiation (V <sub>DS</sub> bias) 4/ | 1019        | V <sub>GS</sub> = 0<br>V <sub>DS</sub> = 80 percent of rated V <sub>DS</sub> (pre-irradiation) |                    |                       |      |                           |      |                        |      |                           |      |       |
| End-point electricals   |             |  |                    |                       |      |                           |      |                        |      |                           |      |       |
| Breakdown voltage, drain to source                            | 3407        | V <sub>GS</sub> = 0;<br>I <sub>D</sub> = 1 mA<br>bias cond. C                                  | V <sub>BRDSS</sub> |                       |      |                           |      |                        |      |                           |      |       |
| 2N7394, 2N7394U   |             |  |                    | 60                    |      | 60                        |      | 60                     |      | 60                        |      | V dc  |
| 2N7268, 2N7268U   |             |  |                    | 100                   |      | 100                       |      | 100                    |      | 100                       |      | V dc  |
| 2N7269, 2N7269U   |             |  |                    | 200                   |      | 200                       |      | 200                    |      | 200                       |      | V dc  |
| 2N7270, 2N7270U   |             |  |                    | 500                   |      | 500                       |      | 500                    |      | 500                       |      | V dc  |
| Gate to source voltage (threshold)                            | 3403        | V <sub>DS</sub> ≥ V <sub>GS</sub><br>I <sub>D</sub> = 1 mA                                     | V <sub>GSth</sub>  |                       |      |                           |      |                        |      |                           |      |       |
| 2N7394, 2N7394U   |             |  |                    | 2                     | 4    | 2                         | 4    | 2                      | 4    | 1.25                      | 4.50 | V dc  |
| 2N7268, 2N7268U   |             |  |                    | 2                     | 4    | 2                         | 4    | 2                      | 4    | 1.25                      | 4.50 | V dc  |
| 2N7269, 2N7269U   |             |  |                    | 2                     | 4    | 2                         | 4    | 2                      | 4    | 1.25                      | 4.50 | V dc  |
| 2N7270, 2N7270U   |             |  |                    | 2                     | 4    | 2                         | 4    | 2                      | 4    | 1.25                      | 4.50 | V dc  |
| Gate current  | 3411        | V <sub>GS</sub> = 20 V<br>V <sub>DS</sub> = 0<br>bias cond. C                                  | I <sub>GSSF1</sub> |                       | 100  |                           | 100  |                        | 100  |                           | 100  | nA dc |
| * Gate current  | 3411        | V <sub>GS</sub> = -20 V<br>V <sub>DS</sub> = 0<br>bias cond. C                                 | I <sub>GSSR1</sub> |                       | -100 |                           | -100 |                        | -100 |                           | -100 | nA dc |

See footnotes at end of table.

TABLE II. Group D inspection - Continued.

| Inspection<br>1/ 2/  | MIL-STD-750 |  | Symbol             | Preirradiation limits |       |                   |       | Postirradiation limits |       |                   |     | Unit |
|--|-------------|--|--------------------|-----------------------|-------|-------------------|-------|------------------------|-------|-------------------|-----|------|
|  | Method      | Conditions   |                    | R                     |       | 3/<br>F, G, and H |       | R                      |       | 3/<br>F, G, and H |     |      |
|  |             |  |                    | Min                   | Max   | Min               | Max   | Min                    | Max   | Min               | Max |      |
| <u>Subgroup 2 - Continued</u><br><br>Drain current<br><br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U | 3413        | Bias cond. C<br>V <sub>GS</sub> = 0<br>V <sub>DS</sub> = 80 percent of rated V <sub>DS</sub> (pre-irradiation) | I <sub>DSS</sub>   |                       |       |                   |       |                        |       |                   |     |      |
|  |             |  |                    |                       | 25    | 25                | 25    | 50                     | μA dc |                   |     |      |
|  |             |  |                    |                       | 25    | 25                | 25    | 50                     | μA dc |                   |     |      |
|  |             |  |                    |                       | 25    | 25                | 25    | 50                     | μA dc |                   |     |      |
| Static drain to source on-state voltage<br><br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U            | 3405        | Condition A<br>V <sub>GS</sub> = 12 V pulsed<br>see 4.5.1<br>I <sub>D</sub> = I <sub>D2</sub>                  | V <sub>DSon1</sub> |                       |       |                   |       |                        |       |                   |     |      |
|  |             |  |                    |                       | 0.81  | 0.81              | 0.81  | 1.2                    | V dc  |                   |     |      |
|  |             |  |                    |                       | 1.365 | 1.365             | 1.365 | 1.89                   | V dc  |                   |     |      |
|  |             |  |                    |                       | 1.6   | 1.6               | 1.6   | 2.48                   | V dc  |                   |     |      |
| * Forward voltage source drain diode<br><br>2N7394, 2N7394U<br>2N7268, 2N7268U<br>2N7269, 2N7269U<br>2N7270, 2N7270U               | 4011        | Condition C,<br>V <sub>GS</sub> = 0<br>I <sub>D</sub> = I <sub>D1</sub>  | V <sub>SD</sub>    |                       |       |                   |       |                        |       |                   |     |      |
|  |             |  |                    |                       | 1.4   | 1.4               | 1.4   | 1.4                    | V dc  |                   |     |      |
|  |             |  |                    |                       | 1.4   | 1.4               | 1.4   | 1.4                    | V dc  |                   |     |      |
|  |             |  |                    |                       | 1.4   | 1.4               | 1.4   | 1.4                    | V dc  |                   |     |      |
|  |             |  |                    | 1.6                   | 1.6   | 1.6               | 1.6   | 1.6                    | V dc  |                   |     |      |

- 1/ For sampling plan, see MIL-PRF-19500. At the manufacturer's option, group D samples need not be subjected to the screening tests, and may be assembled in its qualified package or in any qualified package that the manufacturer has data to correlate the performance to the designated package.
- 2/ Group D qualification may be performed anytime prior to lot formation. Wafers qualified to these group D QCI requirements may be used for any other specification sheet utilizing the same die design.
- 3/ The F designation represent devices which pass end-points at both 100 k and 300 k rads (Si). The G designation represents devices which pass 100 k, 300 k, and 500 k rad (Si) end-points. H must meet end-points for 100 k, 300 k, 500 k and 1,000 k RAD (Si).
- 4/ Separate samples shall be pulled for each bias.

TABLE III. Group E inspection (all quality levels) for qualification or re-qualification only.

| Inspection   | MIL-STD-750 |   | Qualification and large lot quality conformance inspection |
|--|-------------|---|--|
|  | Method      | Conditions  |  |
| <u>Subgroup 1</u>  |             |   | 45 devices<br>c = 0  |
| Thermal shock<br>(temperature cycling)   | 1051        | Test condition G.   |  |
| Hermetic seal<br>Fine leak<br>Gross leak   | 1071        | As applicable.  |  |
| Electrical measurements  |             | See <a href="#">table I</a> , subgroup 2.   |  |
| <u>Subgroup 2 1/</u>   |             |   | 45 devices<br>c = 0  |
| Steady-state gate bias   | 1042        | Condition B, 1,000 hours.   |  |
| Electrical measurements  |             | See <a href="#">table I</a> , subgroup 2.   |  |
| Steady-state reverse bias  | 1042        | Condition A, 1,000 hours.   |  |
| Electrical measurements  |             | See <a href="#">table I</a> , subgroup 2.   |  |
| <u>Subgroup 4</u>  |             |   | Sample size<br>N/A   |
| Thermal impedance curves   |             | See <a href="#">MIL-PRF-19500</a> .   |  |
| <u>Subgroup 5</u>  |             |   | 3 devices<br>c = 0   |
| Barometric pressure<br>(2N7270, 2N7270U only)  | 1001        | Test condition C. For device type 2N7270, 2N7270U: $V_{DS} = 500 \text{ V}$ ; $I_{(ISO)} < 0.25 \text{ mA}$ . |  |
| <u>Subgroup 10</u>   |             |   | 22 devices<br>c = 0  |
| Commutating diode for safe operating area test procedure for measuring dv/dt during reverse recovery of power MOSFET transistors or insulated gate bipolar transistors | 3476        | Test conditions shall be derived by the manufacturer.   |  |

1/ A separate sample may be pulled for each test condition.

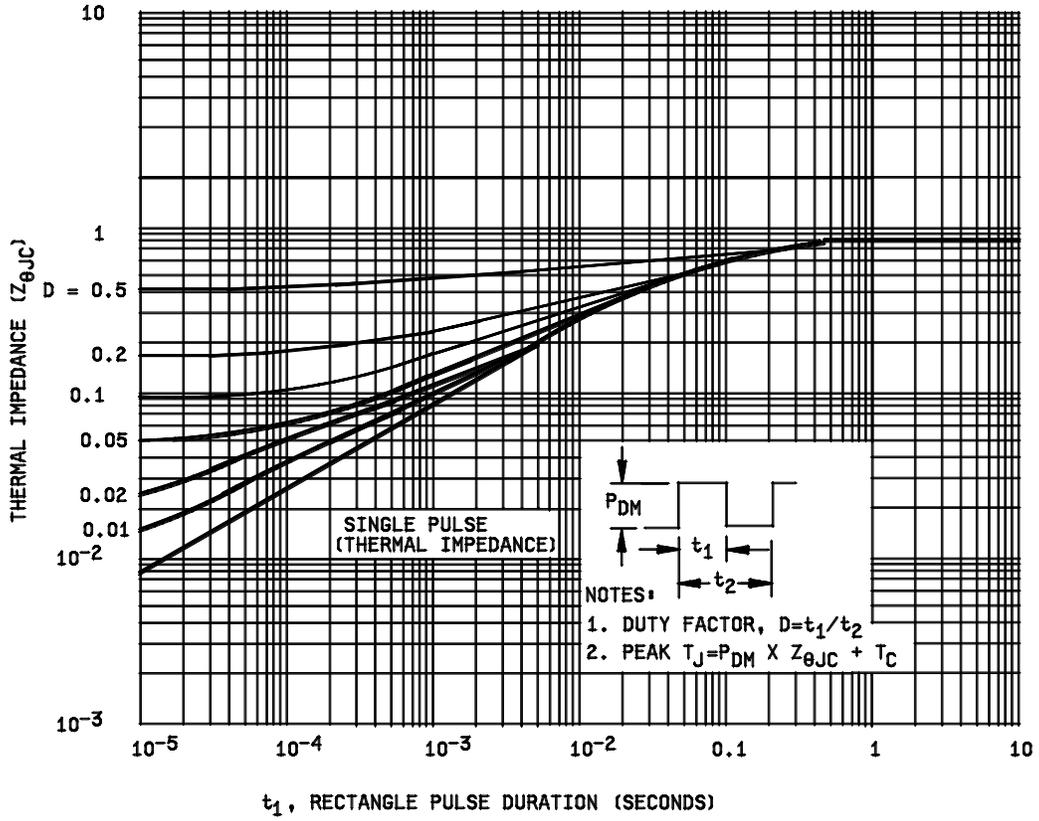
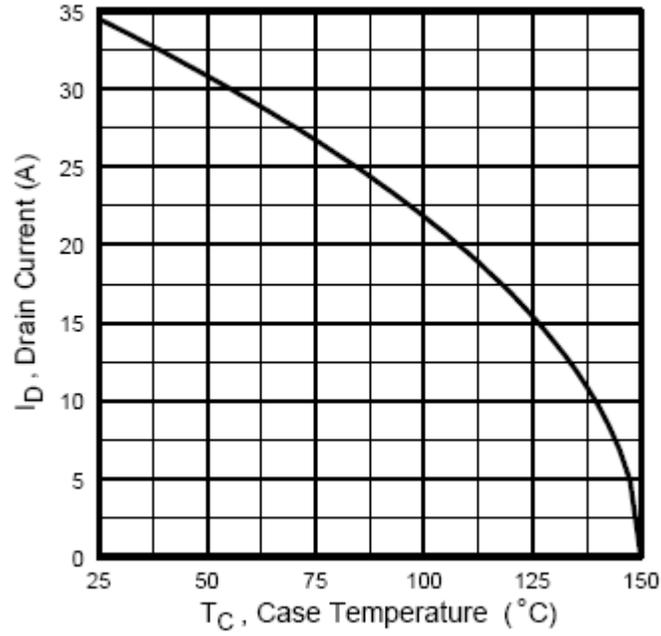


FIGURE 3. Thermal impedance curves.

MIL-PRF-19500/603K

2N7268, 2N7268U



2N7269, 2N7269U

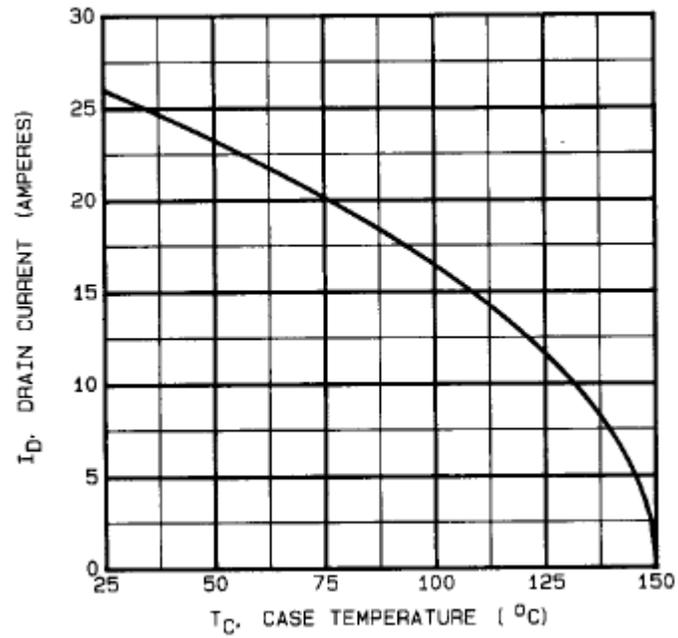
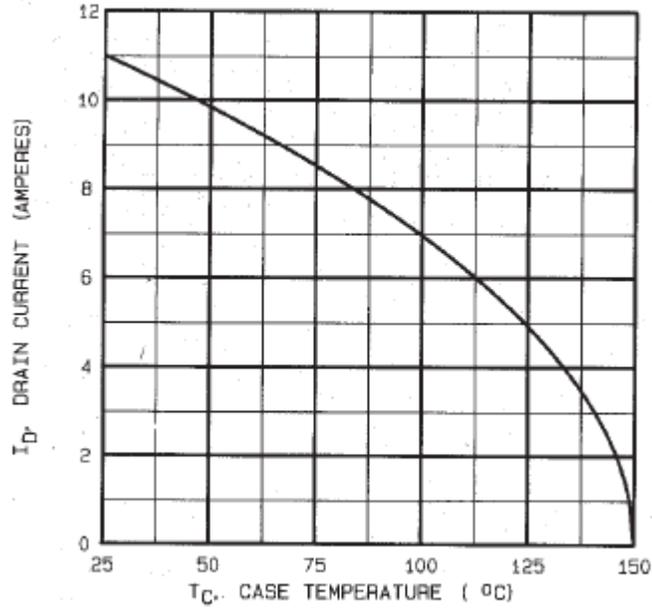


FIGURE 4. Maximum drain current vs case temperature.  
2N7270, 2N7270U



2N7394, 2N7394U

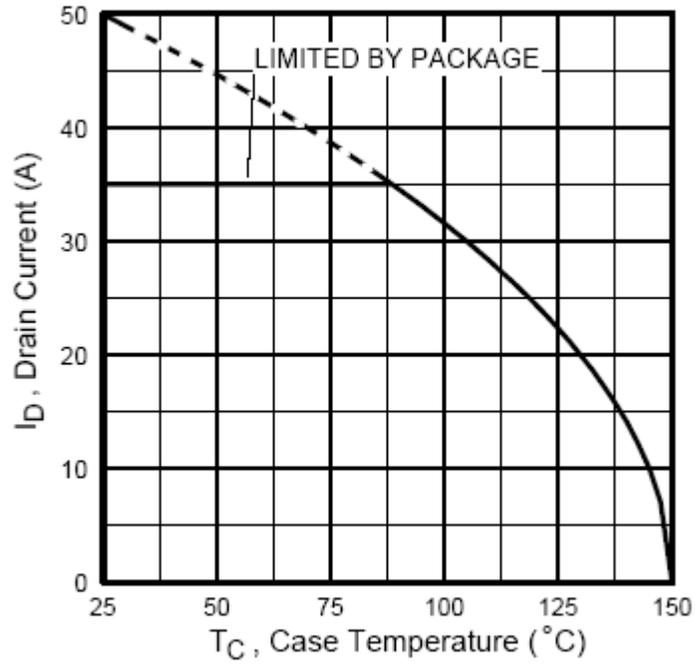
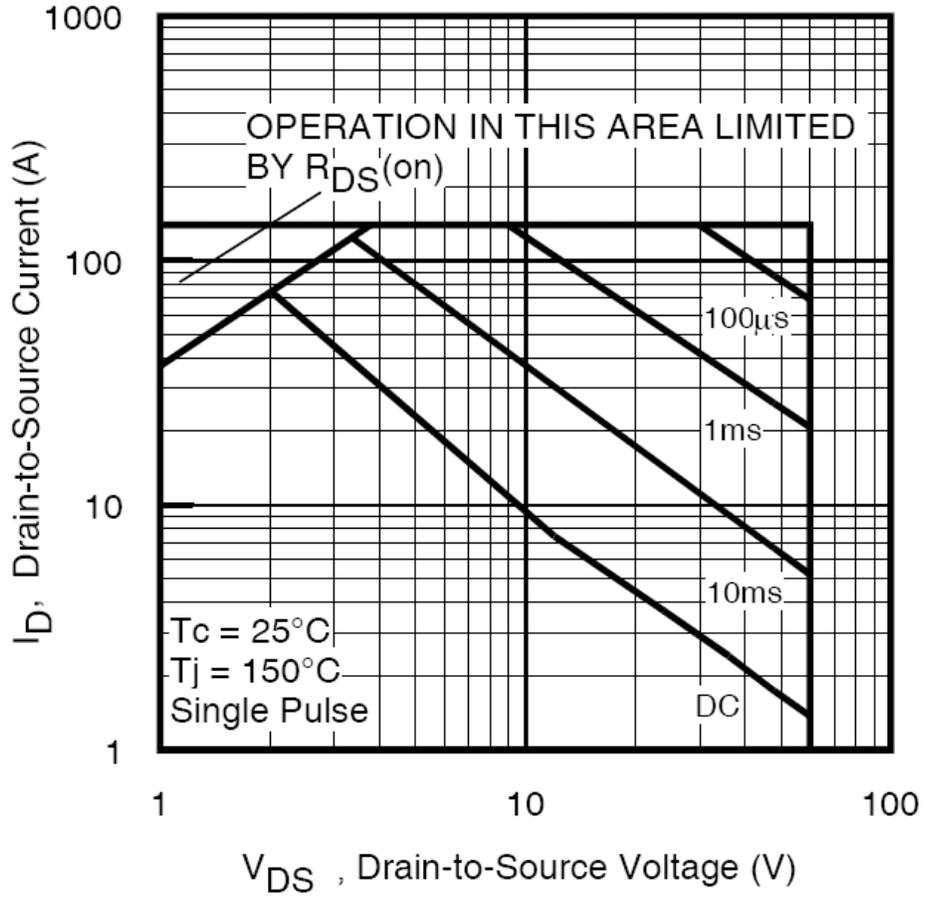


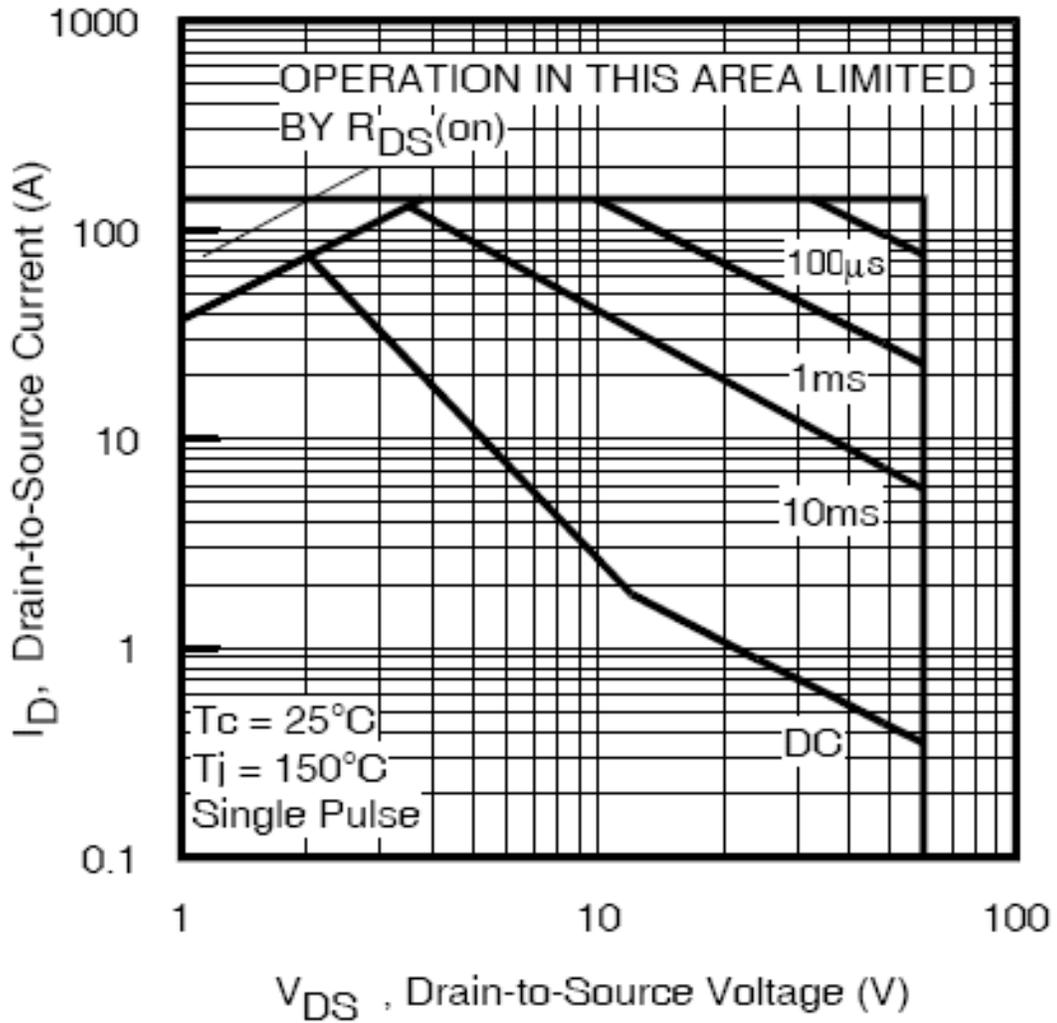
FIGURE 4. Maximum drain current vs case temperature - Continued.



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FIGURE 5. Safe operating area graph.

2N7394U



\*

FIGURE 5. Safe operating area graphs - Continued.

2N7268

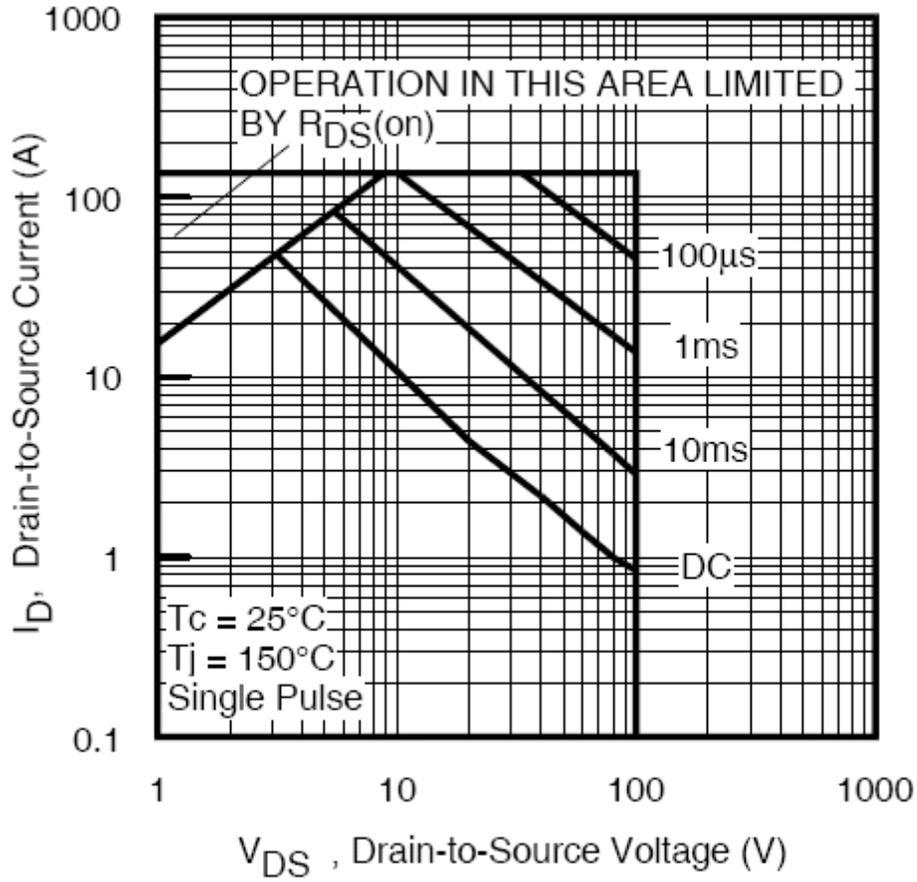


FIGURE 6. Safe operating area graph.

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2N7268U

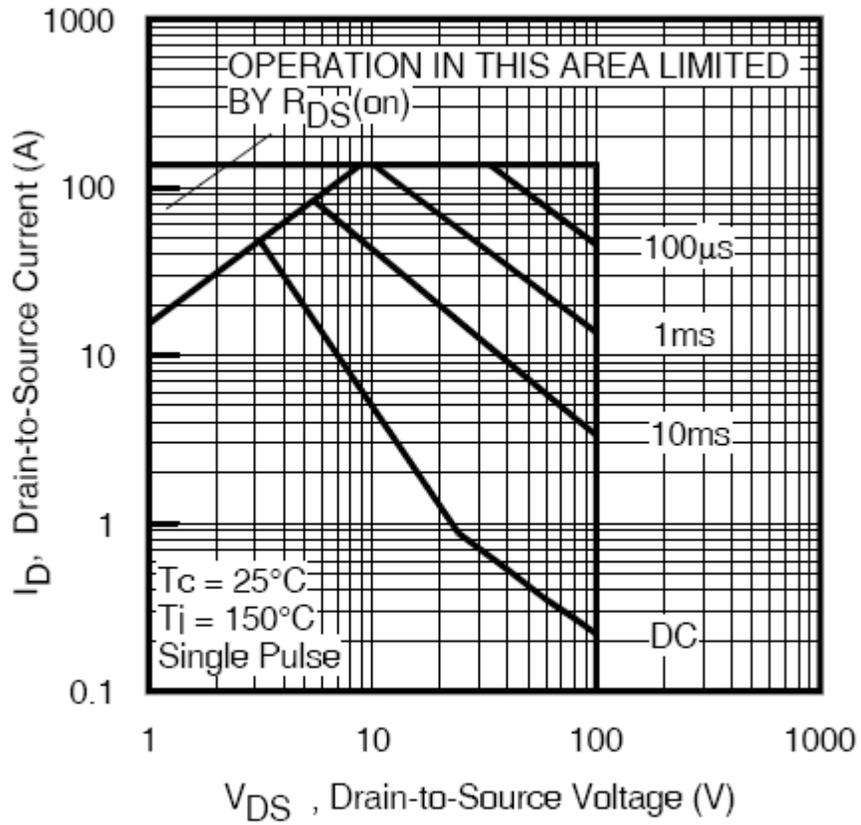
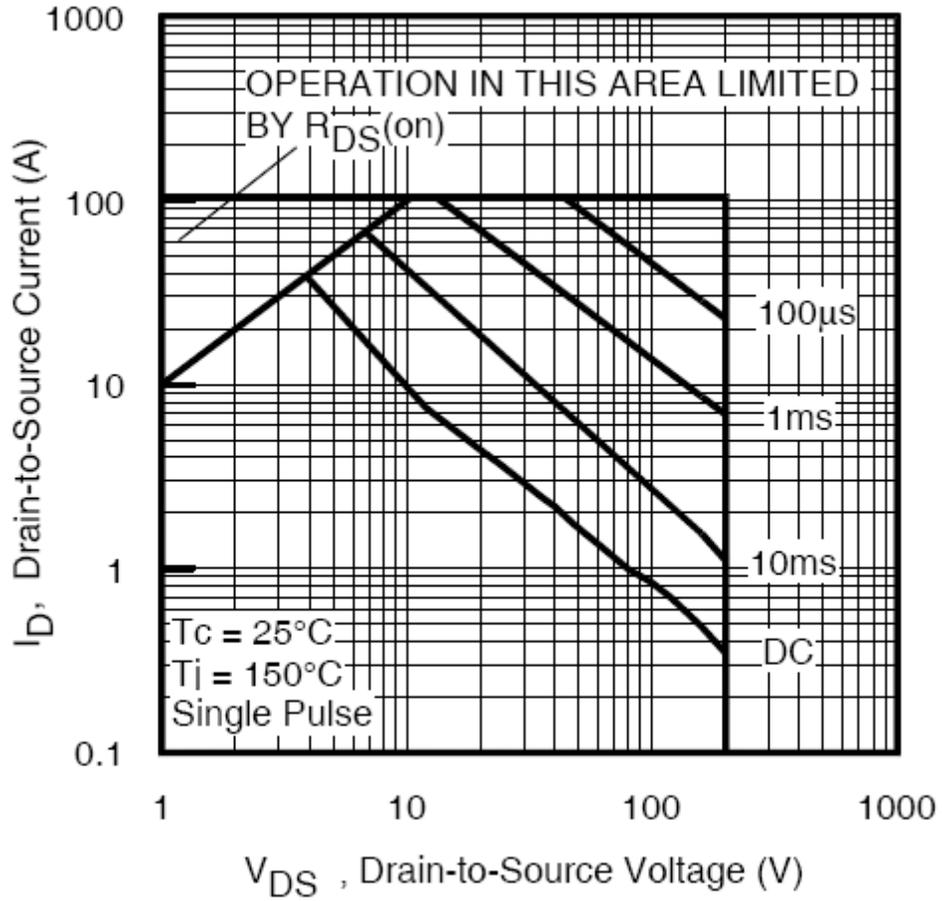


FIGURE 6. Safe operating area graph - Continued.

2N7269



\*

FIGURE 7. Safe operating area graph.

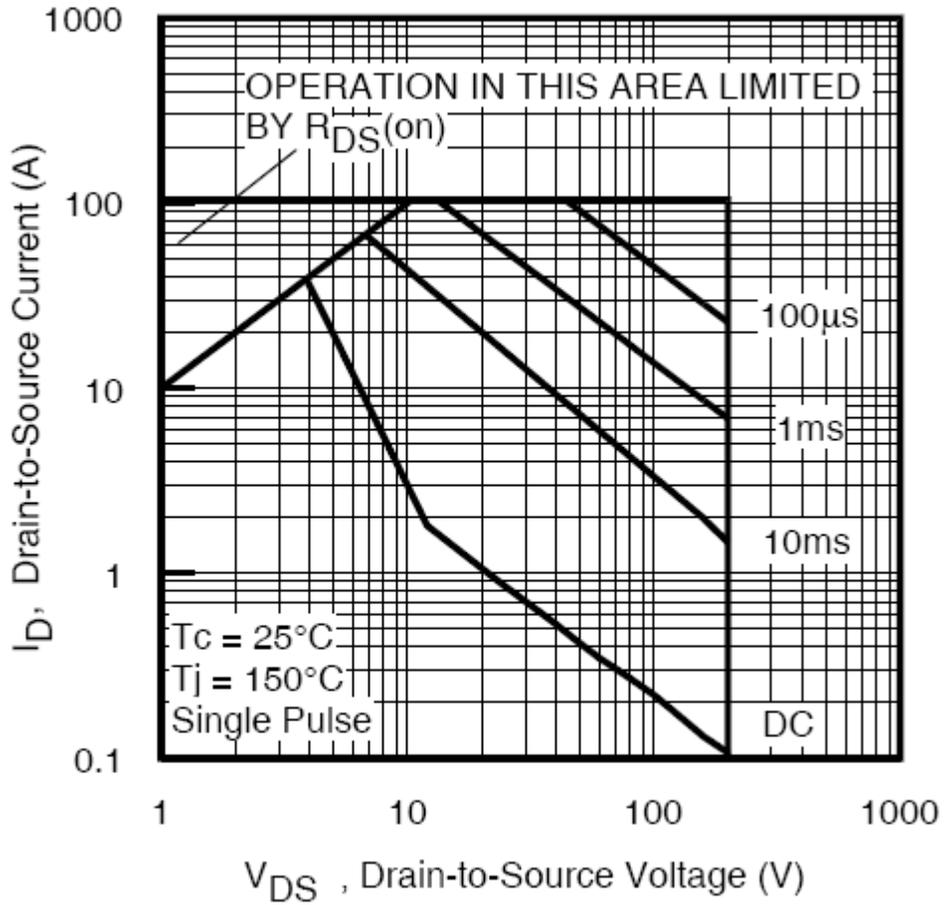


FIGURE 7. Safe operating area graph - Continued.

2N7270

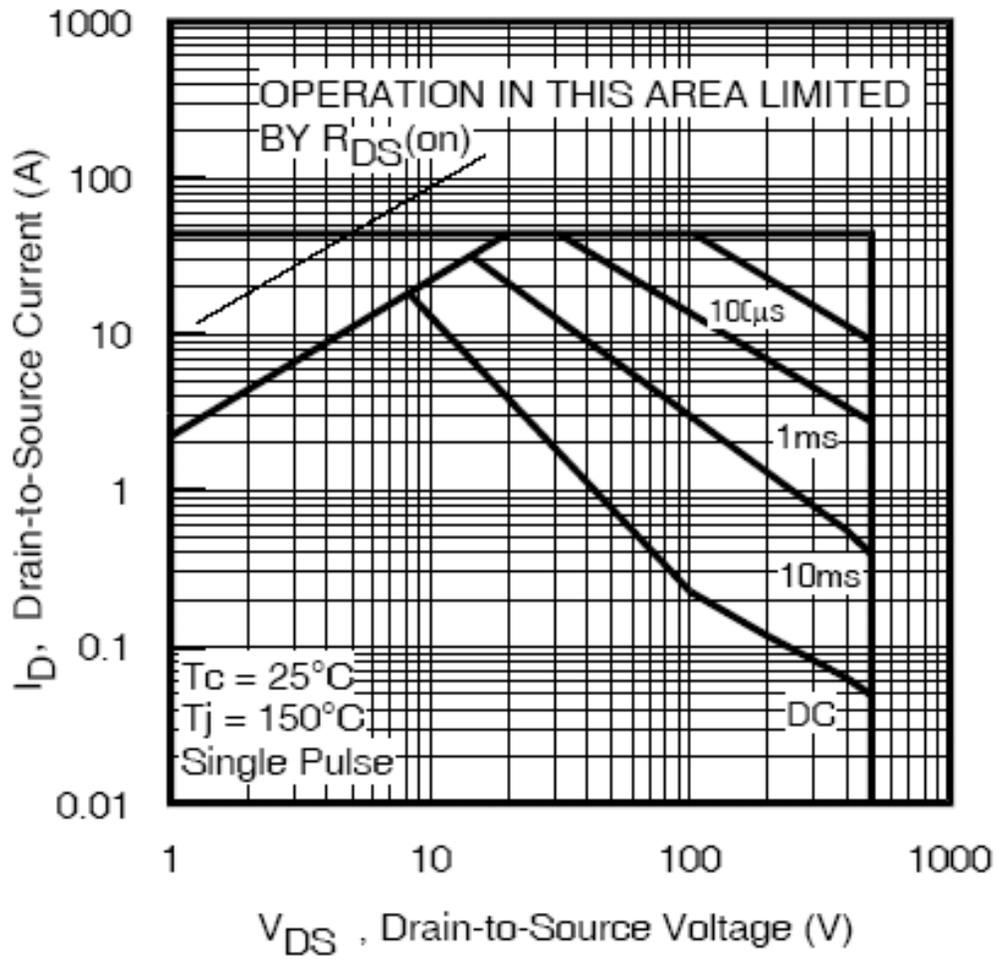


FIGURE 8. Safe operating area graph.

2N7270U

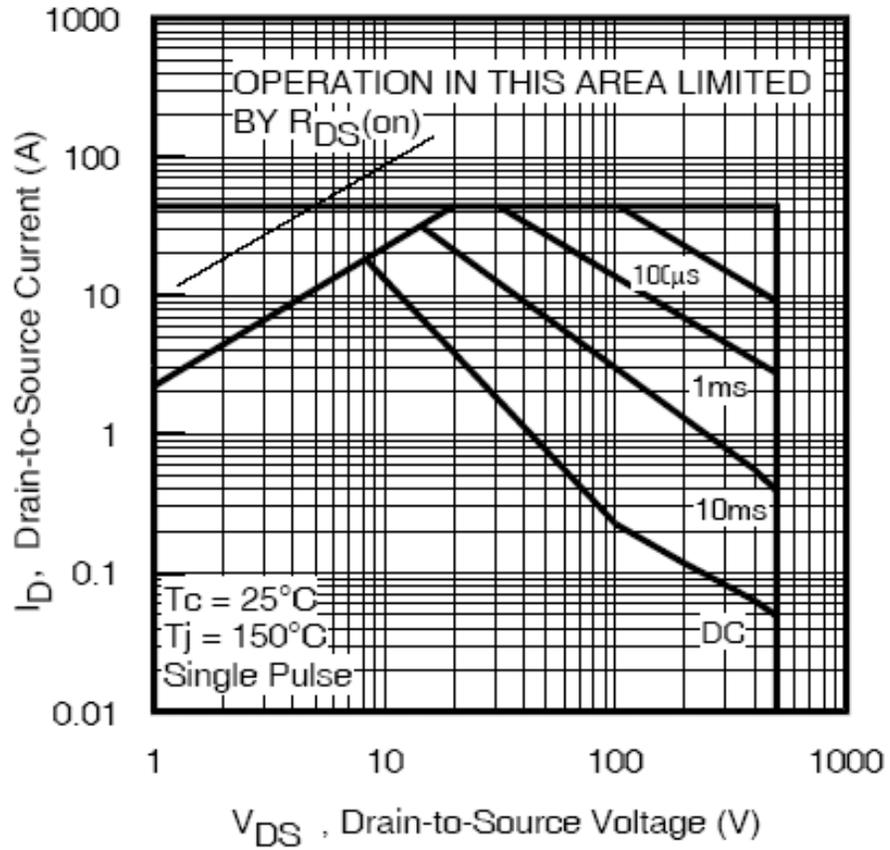


FIGURE 8. Safe operating area graph - Continued.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in [MIL-PRF-19500](#) are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

- \* 6.2 Acquisition requirements. Acquisition documents should specify the following:
  - a. Title, number, and date of this specification.
  - b. Packaging requirements (see 5.1).
  - c. Lead finish (see [3.4.1](#)).
  - \* d. The complete PIN, see [1.5](#) and [6.6](#).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail [vqe.chief@dla.mil](mailto:vqe.chief@dla.mil). An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

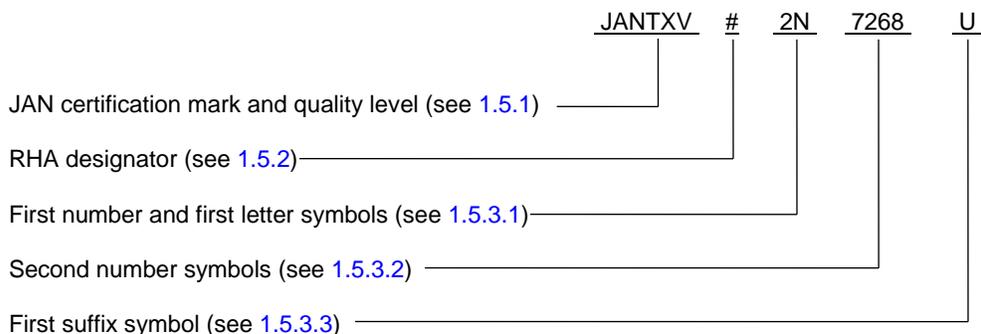
6.4 Substitution information. Devices covered by this specification are substitutable for the manufacturer's and user's Part or Identifying Number (PIN). This information in no way implies that manufacturer's PIN's are suitable for the military PIN.

| Preferred types | Commercial types (1) |          |
|-----------------|----------------------|----------|
|                 | TO254-AA             | "U"      |
| 2N7394          | IRHM7054             | IRHN7054 |
| 2N7268          | IRHM7150             | IRHN7150 |
| 2N7269          | IRHM7250             | IRHN7250 |
| 2N7270          | IRHM7450             | IRHN7450 |

- (1) IRH 7: 100k RAD (Si)
- IRH 3: 300k RAD (Si)
- IRH 4: 600k RAD (Si)
- IRH 8: 1,000k RAD (Si)

\* 6.5 PIN construction example.

\* 6.5.1 Encapsulated devices The PINs for encapsulated devices are constructed using the following form.



\* 6.6 List of PINs.

\* 6.6.1 List of PINs for encapsulated devices. The following is a list of possible PINs for encapsulated devices available on this specification sheet.

| PINs for devices of the "TXV" quality level | PINs for devices of the "S" quality level |
|---|---|
| JANTXV#2N7268                               | JANS#2N7268                               |
| JANTXV#2N7269                               | JANS#2N7269                               |
| JANTXV#2N7270                               | JANS#2N7270                               |
| JANTXV#2N7394                               | JANS#2N7394                               |

(1) The pound symbol (#) represents the RHA level of "R", "F", "G", or "H".

6.7 JANC die versions. The JANHC and JANKC die versions of these devices are covered under specification sheet [MIL-PRF-19500/657](#).

\* 6.8 Request for new types and configurations. Requests for new device types or configurations for inclusions in this specification sheet should be submitted to: DLA Land and Maritime, ATTN: VAC, Post Office Box 3990, Columbus, OH 43218-3990 or by electronic mail at [Semiconductor@dla.mil](mailto:Semiconductor@dla.mil) or by facsimile (614) 693-1642 or DSN 850-6939.

6.9 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:  
Army - CR  
Navy - EC  
Air Force - 85  
NASA - NA  
DLA - CC

Preparing activity:  
DLA - CC  
  
(Project 5961-2016-002)

Review activities:  
Navy - AS  
Air Force - 19, 70

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil/>.